

Excellent Integrated System Limited

Stocking Distributor

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<u>Vishay Semiconductor/Diodes Division</u> <u>VS-16CDU06-M3/I</u>

For any questions, you can email us directly: sales@integrated-circuit.com

Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of VS-16CDU06-M3/I - DIODE UFAST REC 600V 16A TO-263A

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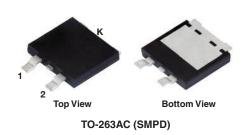
VS-16CDU06-M3

HALOGEN

FREE

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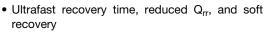
Ultrafast Rectifier, 2 x 8 A FRED Pt®

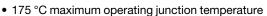




PRODUCT SUMMARY				
Package	TO-263AC (SMPD)			
I _{F(AV)}	2 x 8 A			
V_{R}	600 V			
V _F at I _F	0.94 V			
t _{rr}	45 ns			
T _J max.	175 °C			
Diode variation	Dual die			

FEATURES





• For PFC CRM, snubber operation

Low forward voltage drop

Low leakage current

• Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

Meets JESD 201 class 2 whisker test

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop, ultrafast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC, boost, in the AC/DC section of SMPS, freewheeling and clamp diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V_{RRM}		600	V
Average rectified forward current per device per diode	per device		T 140 °C	16	
	per diode	IF(AV)	T _{solder pad} = 149 °C	8	
Non-repetitive peak surge current	per device	l i	T _J = 25 °C, 6 ms square pulse	200	А
	per diode	I _{FSM}		105	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS MIN. TYP. MA		MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	
Forward voltage, per diode V _F	W	I _F = 8 A	-	1.1	1.4	V
	v _F	I _F = 8 A, T _J = 150 °C	-	0.94	1.15	
December 1 and 1 and 1 and 1 and 1	_	$V_R = V_R$ rated	-	-	5	
Reverse leakage current, per diode I _R		T _J = 150 °C, V _R = V _R rated	-	20	150	μΑ
Junction capacitance, per diode	C _T	V _R = 600 V	-	8	-	pF

Revision: 10-Feb-15 Document Number: 95814

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	45	-	
Reverse recovery time		I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	-	60	
	t _{rr}	T _J = 25 °C	I _F = 8 A, dI _F /dt = 500 A/μs, V _B = 400 V	-	70	-	ns
		T _J = 125 °C		-	100	-	
Peak recovery current I _{RRM}	,	T _J = 25 °C		-	12	-	^
	IRRM	T _J = 125 °C		-	17	-	A
Davis and a second about	0	T _J = 25 °C		-	430	-	
Reverse recovery charge	everse recovery charge Q _{rr}	T _J = 125 °C		-	850	-	nC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	+175	°C
Thermal resistance, per diode junction to solder pad	R _{thJ-Sp}		-	1.8	2.5	°C/W
Approximate weight				0.55		g
Approximate weight				0.02		oz.
Marking device		Case style TO-263AC (SMPD)	16CDU06			

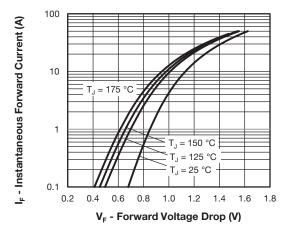


Fig. 1 - Typical Forward Voltage Drop Characteristics

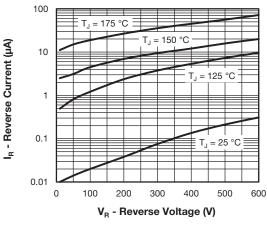


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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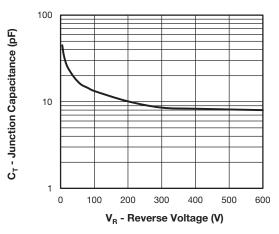


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

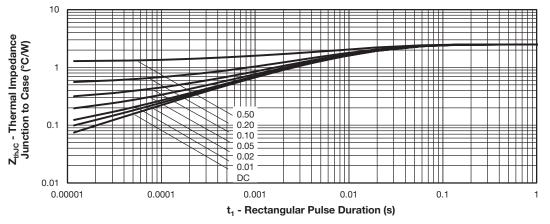


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

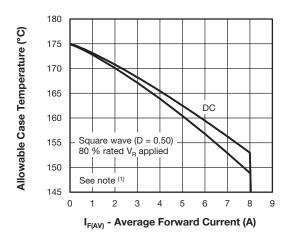


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

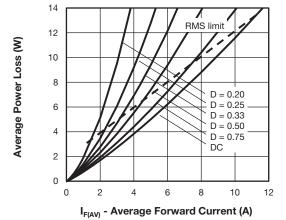


Fig. 6 - Forward Power Loss Characteristics

Note

Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; Pd = Forward power loss = $I_{F(AV)}x$ V_{FM} at $(I_{F(AV)}/D)$ (see fig. 5); Pd_{REV} = Inverse power loss = V_{R1} x I_{R} (1 - D); I_{R} at V_{R1} = rated V_{R}

Revision: 10-Feb-15 3 Document Number: 95814

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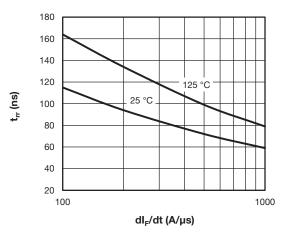


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

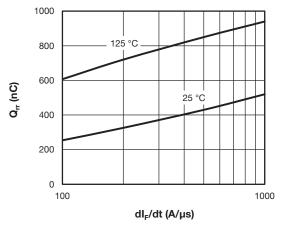
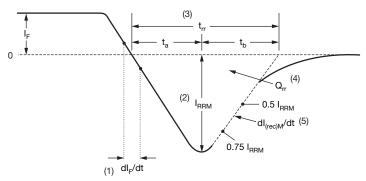


Fig. 8 - Typical Stored Charge vs. dl_F/dt



- (1) dl_F/dt rate of change of current through zero crossing
- (2) $\rm I_{RRM}$ peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RBM}$ and 0.50 $\rm I_{RBM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

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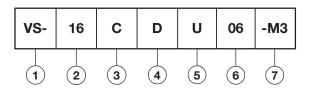


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ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- Current rating (16 A)
- 3 Circuit configuration:
 - C = common cathode
- D = SMPD package
- 5 Process type,
 - U = ultrafast recovery
- 6 Voltage code (06 = 600 V)
- 7 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION					
VS-16CDU06-M3/I	2000	2000	13" diameter plastic tape and reel		

LINKS TO RELATED DOCUMENTS			
Dimensions <u>www.vishay.com/doc?95604</u>			
Part marking information	www.vishay.com/doc?95566		
Packaging information	www.vishay.com/doc?88869		



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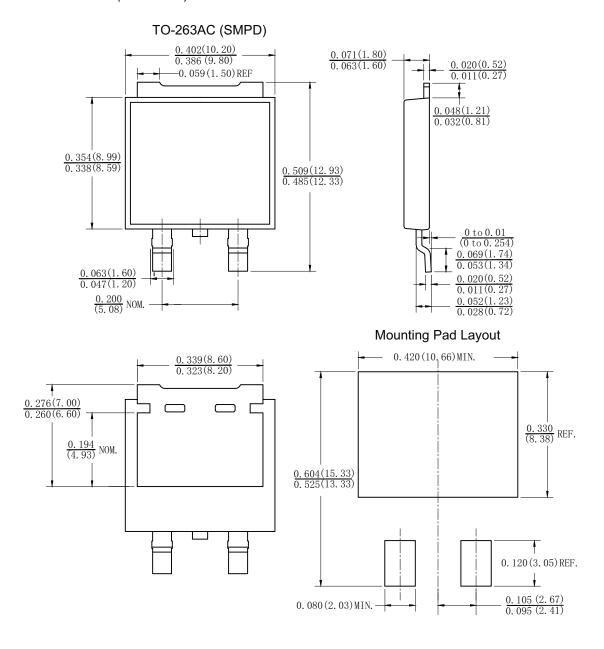


Outline Dimensions

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TO-263AC (SMPD)

DIMENSIONS in inches (millimeters)





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Revision: 13-Jun-16 Document Number: 91000 1